

7MBR35VW120-50

IGBT Modules

IGBT MODULE (V series)

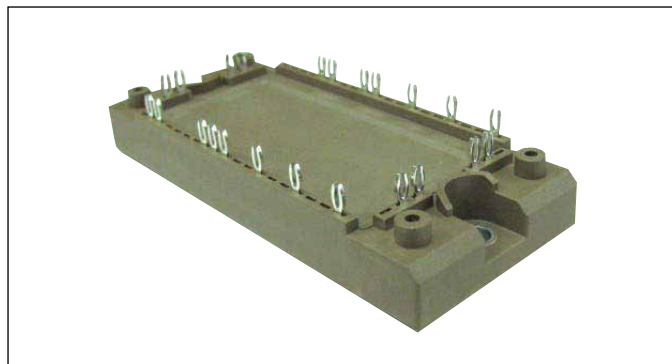
1200V / 35A / PIM

■ Features

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant product

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at $T_c=25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units
Inverter	Collector-Emitter voltage	V _{CES}			1200	V
	Gate-Emitter voltage	V _{GES}			±20	V
	Collector current	I _c	Continuous	T _c =100°C	35	A
		I _{cp}	1ms	T _c =80°C	70	
		-I _c			35	
		-I _c pulse	1ms	70		
	Collector power dissipation	P _c	1 device		210	W
Brake	Collector-Emitter voltage	V _{CES}			1200	V
	Gate-Emitter voltage	V _{GES}			±20	V
	Collector current	I _c	Continuous	T _c =80°C	25	A
		I _{cP}	1ms	T _c =80°C	50	
	Collector power dissipation	P _c	1 device		170	W
	Repetitive peak reverse voltage (Diode)	V _{RRM}			1200	V
Converter	Repetitive peak reverse voltage	V _{RRM}			1600	V
	Average output current	I _o	50Hz/60Hz, sine wave		35	A
	Surge current (Non-Repetitive)	I _{FSM}	10ms, T _j =150°C		260	A
	I ² t (Non-Repetitive)	I ² t	half sine wave		338	A ² s
Junction temperature		T _j	Inverter, Brake		175	°C
			Converter		150	
Operating junciton temperature (under switching conditions)		T _{jop}	Inverter, Brake		150	
			Converter		150	
Case temperature		T _c			125	
Storage temperature		T _{stg}			-40 to +125	
Isolation voltage	between terminal and copper base (*1) between thermistor and others (*2)	V _{iso}	AC : 1min.		2500	VAC
Screw torque	Mounting (*3)	-	M5		3.5	N m

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable value : 2.5-3.5 Nm (M5)

● Electrical characteristics (at T_j = 25°C unless otherwise specified)

Items		Symbols	Conditions		Characteristics			Units
					min.	typ.	max.	
Inverter	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V, V _{CE} = 1200V		-	-	1.0	mA
	Gate-Emitter leakage current	I _{GES}	V _{GE} = 0V, V _{GE} = ±20V		-	-	200	nA
	Gate-Emitter threshold voltage	V _{GE (th)}	V _{CE} = 20V, I _C = 35mA		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	V _{GE} = 15V I _C = 35A	T _J =25°C	-	2.15	2.60	V
				T _J =125°C	-	2.50	-	
				T _J =150°C	-	2.55	-	
		V _{CE (sat)} (chip)	V _{GE} = 15V I _C = 35A	T _J =25°C	-	1.85	2.30	
				T _J =125°C	-	2.20	-	
	T _J =150°C	-	2.25	-				
	Internal gate resistance	R _{g(int)}	-		-	0	-	Ω
	Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz		-	2.9	-	nF
	Turn-on time	ton	V _{CC} = 600V I _C = 35A V _{GE} = +15 / -15V		-	0.39	1.20	μs
		tr			-	0.09	0.60	
		tr (i)			-	0.03	-	
	Turn-off time	toff	R _G = 27Ω		-	0.53	1.00	
		tf			-	0.06	0.30	
	Forward on voltage	V _F (terminal)	I _F = 35A	T _J =25°C	-	2.00	2.45	V
T _J =125°C				-	2.15	-		
T _J =150°C				-	2.10	-		
V _F (chip)		I _F = 35A	T _J =25°C	-	1.70	2.15		
			T _J =125°C	-	1.85	-		
T _J =150°C	-	1.80	-					
Reverse recovery time	trr	I _F = 35A		-	-	0.35	μs	
Brake	Zero gate voltage collector current	I _{CES}	V _{GE} = 0V V _{CE} = 1200V		-	-	1.0	mA
	Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V V _{GE} = +20 / -20V		-	-	200	nA
	Collector-Emitter saturation voltage	V _{CE (sat)} (terminal)	V _{GE} = 15V I _C = 25A	T _J =25°C	-	2.05	2.50	V
				T _J =125°C	-	2.40	-	
				T _J =150°C	-	2.45	-	
		V _{CE (sat)} (chip)	V _{GE} = 15V I _C = 25A	T _J =25°C	-	1.85	2.30	
				T _J =125°C	-	2.20	-	
	T _J =150°C	-	2.25	-				
	Internal gate resistance	R _{g(int)}	-		-	0	-	Ω
	Turn-on time	ton	V _{CE} = 600V I _C = 25A		-	0.39	1.20	μs
		tr			-	0.09	0.60	
	Turn-off time	toff	V _{GE} = +15 / -15V R _G = 39Ω		-	0.53	1.00	
tf		-			0.06	0.30		
Reverse current	IRRM	V _R = 1200V		-	-	1.00	mA	
Converter	Forward on voltage	V _{FM} (chip)	I _F = 35A	terminal	-	1.65	2.10	V
				chip	-	1.35	-	
	Reverse current	IRRM	V _R = 1600V		-	-	1.0	mA
Thermistor	Resistance	R	T = 25°C		-	5000	-	Ω
			T = 100°C		465	495	520	
	B value	B	T = 25 / 50°C		3305	3375	3450	K

● Thermal resistance characteristics

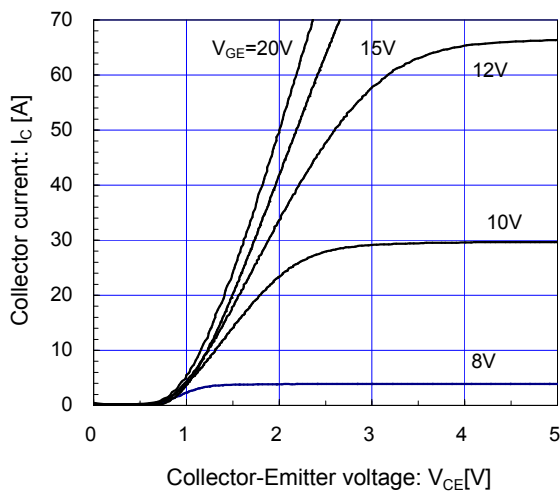
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	Inverter IGBT	-	-	0.72	°C/W
		Inverter FWD	-	-	0.91	
		Brake IGBT	-	-	0.89	
		Converter Diode	-	-	0.88	
Contact thermal resistance (1device) (*4)	R _{th(c-f)}	with Thermal Compound	-	0.05	-	

Note *4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

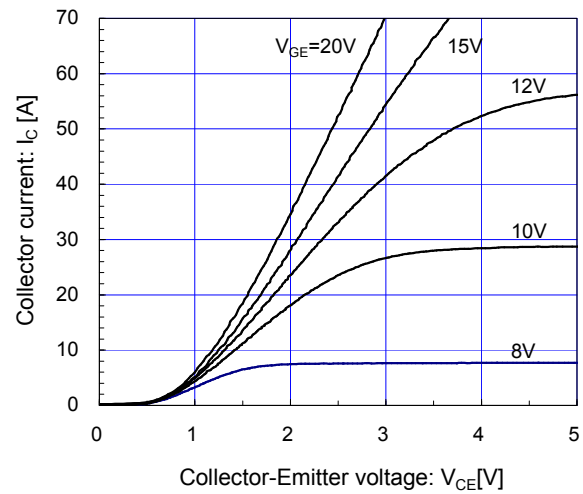
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

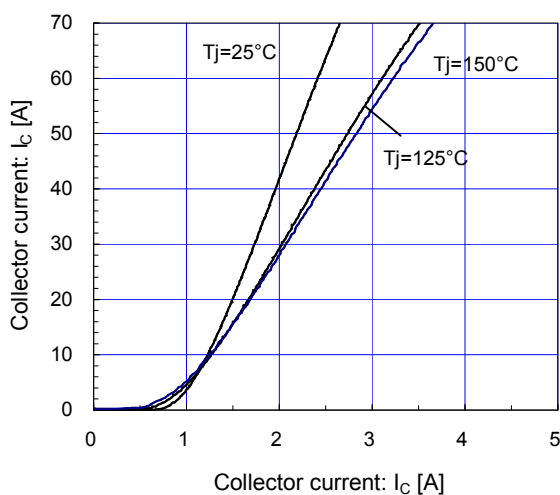
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Collector current vs. Collector-Emittor voltage (typ.)

 $T_j = 150^\circ\text{C}$ / chip

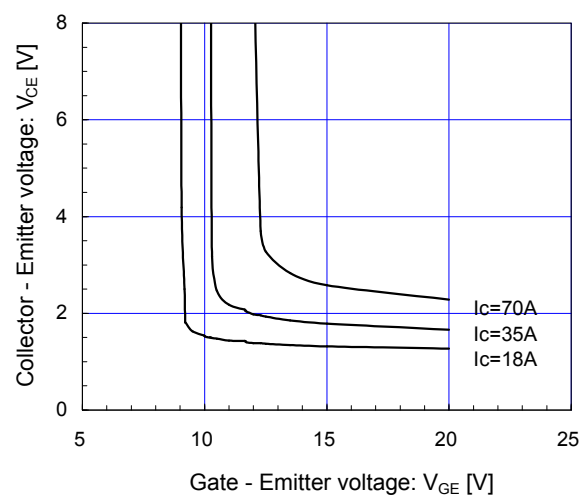
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

 $V_{GE} = 15\text{V}$ / chip

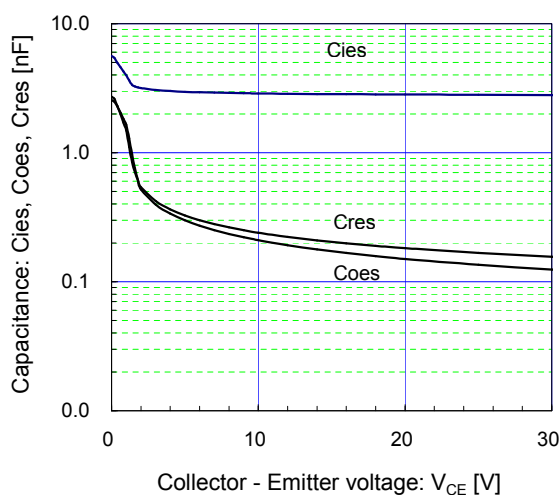
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Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

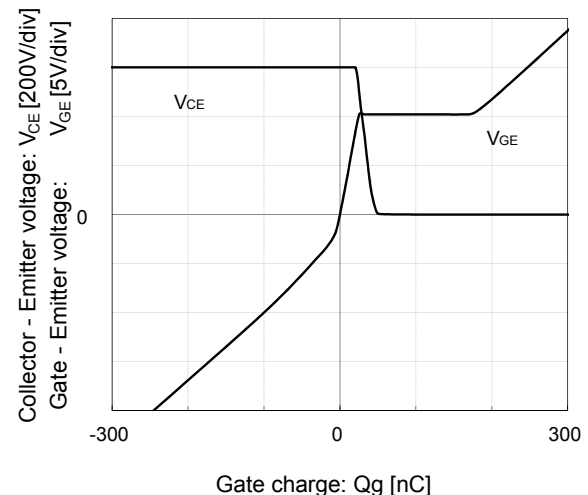
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Capacitance vs. Collector-Emittor voltage (typ.)

 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$ 

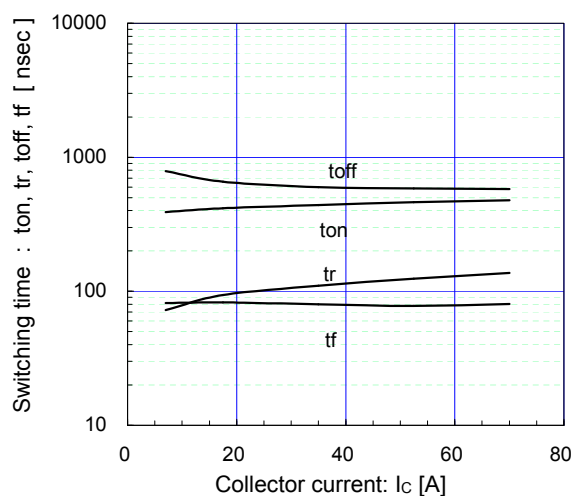
[Inverter]

Dynamic gate charge (typ.)

 $V_{CC} = 600\text{V}$, $I_C = 35\text{A}$, $T_j = 25^\circ\text{C}$ 

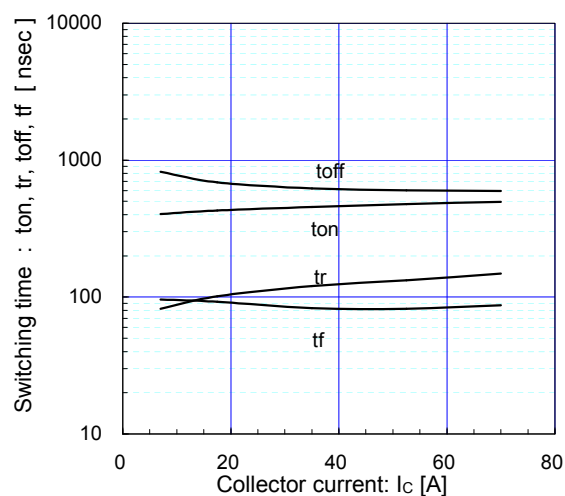
[Inverter]

Switching time vs. Collector current (typ.)
 $V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=27\Omega$, $T_j=125^\circ C$



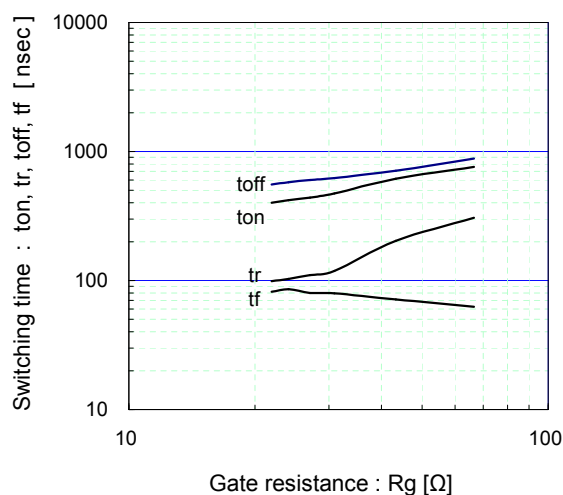
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Switching time vs. Collector current (typ.)
 $V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=27\Omega$, $T_j=150^\circ C$



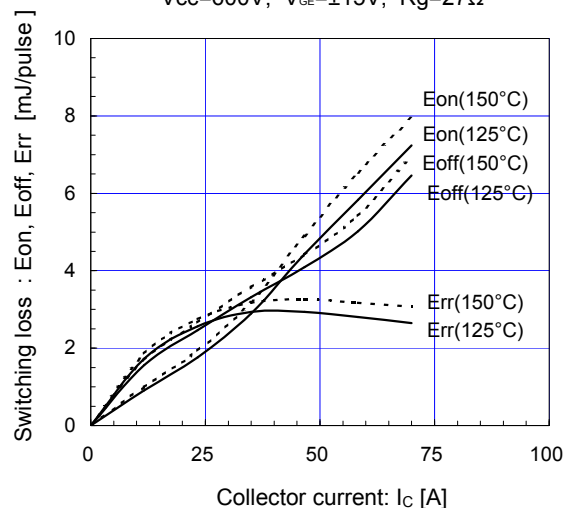
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Switching time vs. gate resistance (typ.)
 $V_{CC}=600V$, $I_c=35A$, $V_{GE}=\pm 15V$, $T_j=125^\circ C$



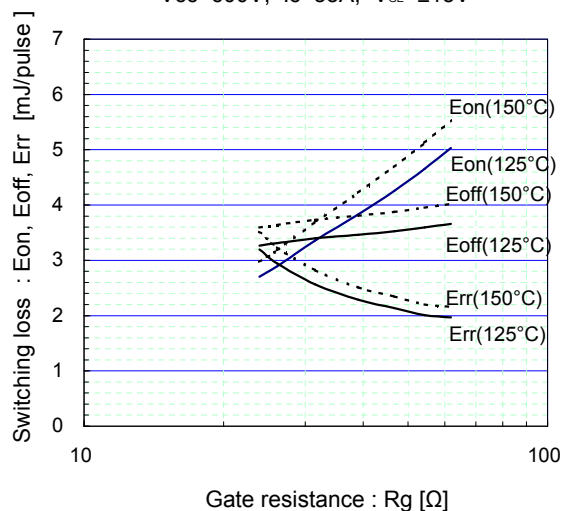
[Inverter] a

Switching loss vs. Collector current (typ.)
 $V_{CC}=600V$, $V_{GE}=\pm 15V$, $R_g=27\Omega$



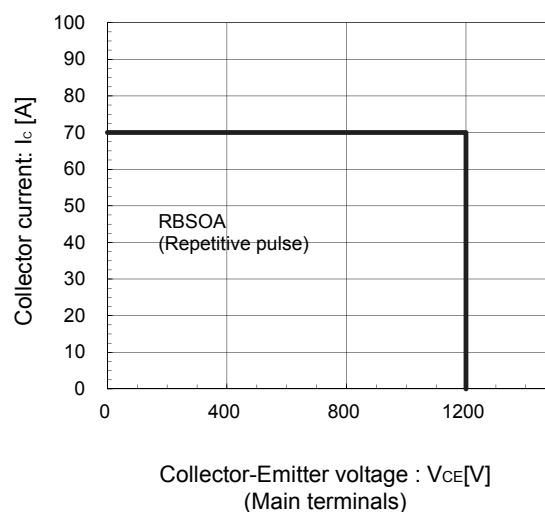
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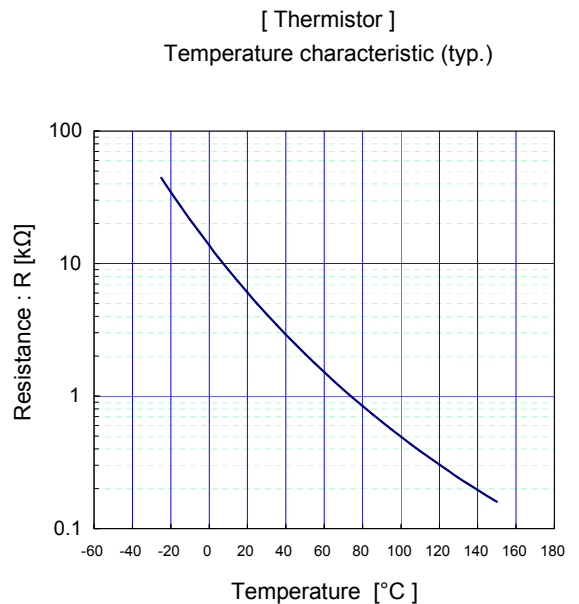
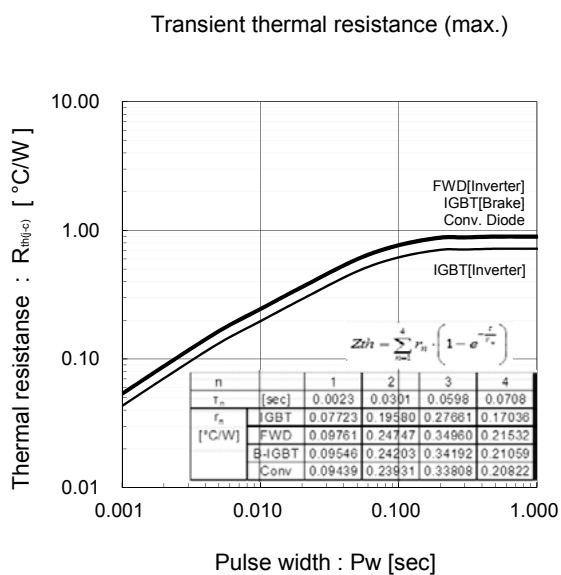
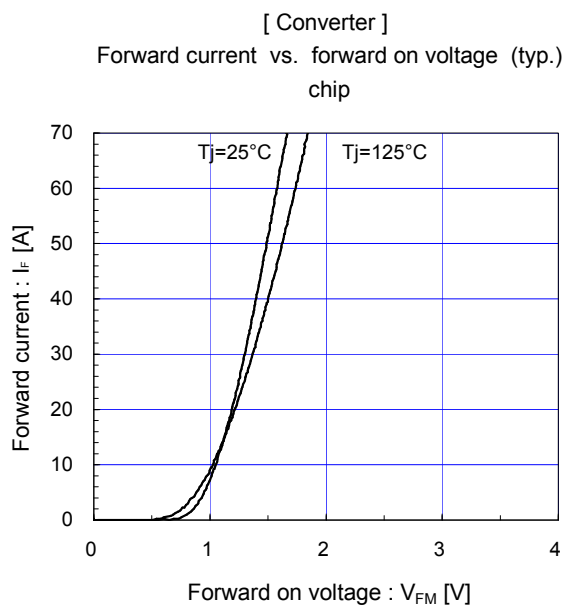
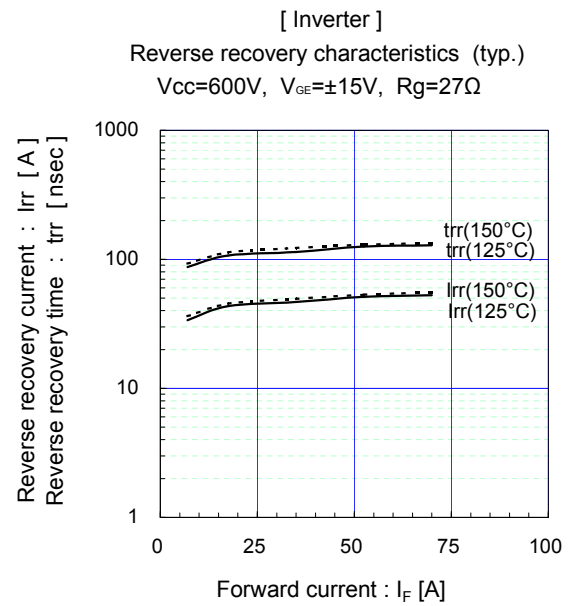
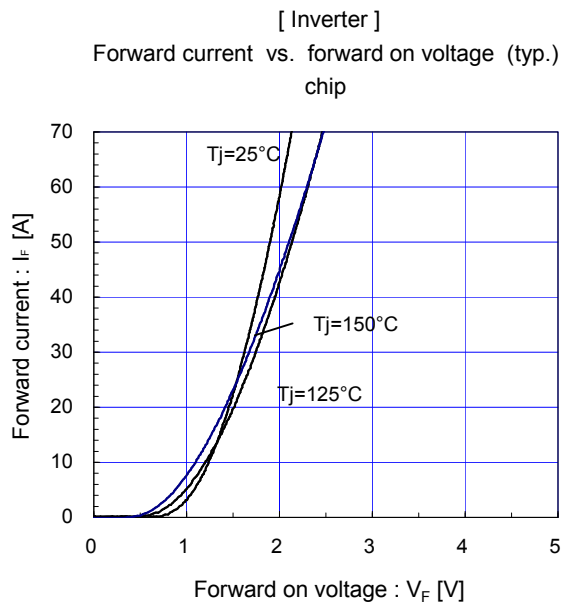
Switching loss vs. gate resistance (typ.)
 $V_{CC}=600V$, $I_c=35A$, $V_{GE}=\pm 15V$



[Inverter]

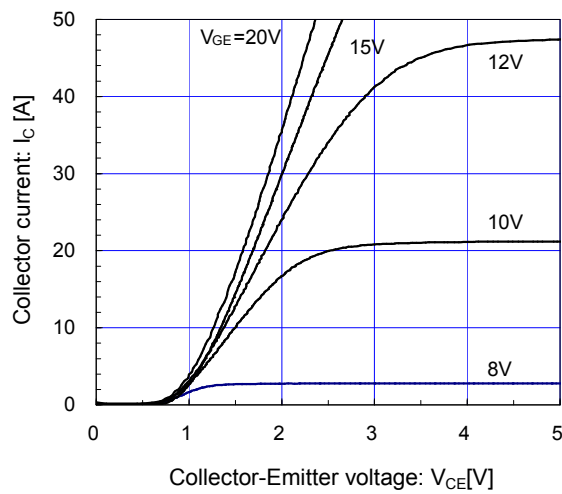
Reverse bias safe operating area (max.)
 $+V_{GE}=15V$, $-V_{GE} \leq 15V$, $R_g \geq 27\Omega$, $T_j = 150^\circ C$





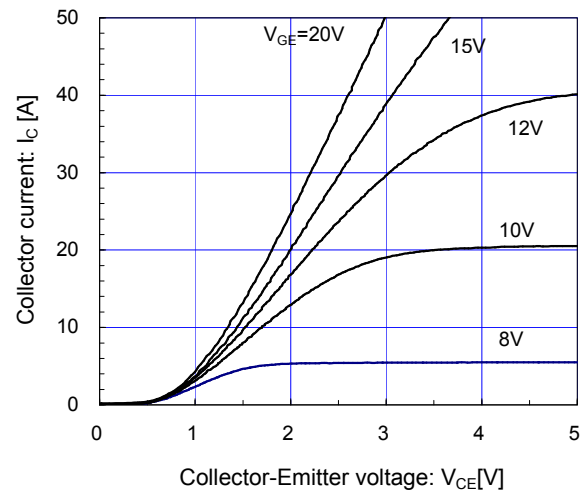
[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

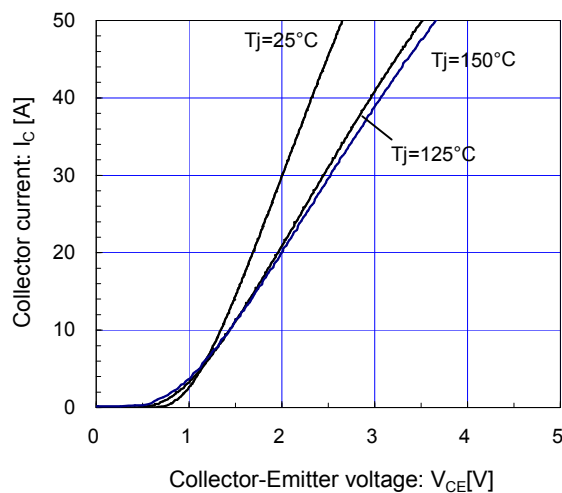
[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

 $T_j = 150^\circ\text{C}$ / chip

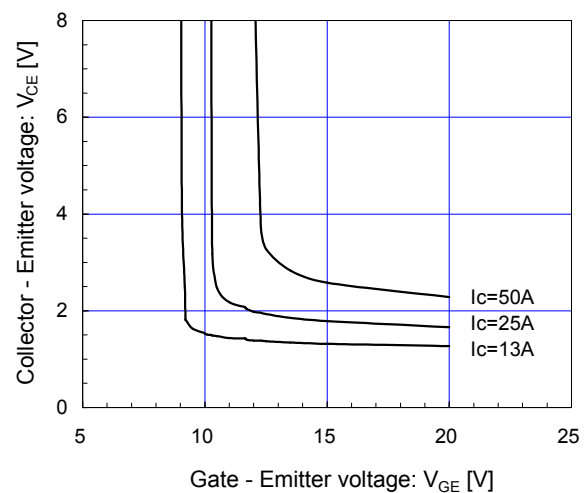
[Brake]

Collector current vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 15\text{V}$ / chip

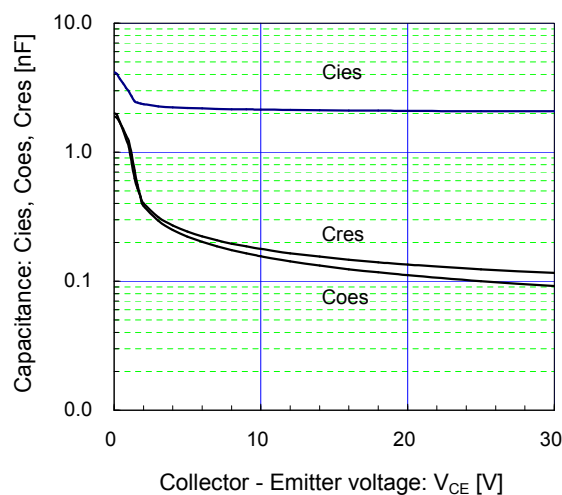
[Brake]

Collector-Emitter voltage vs. Gate-Emitter voltage (typ.)

 $T_j = 25^\circ\text{C}$ / chip

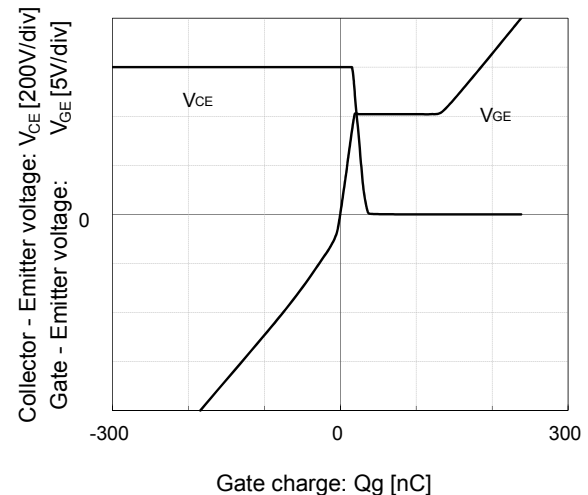
[Brake]

Capacitance vs. Collector-Emitter voltage (typ.)

 $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_j = 25^\circ\text{C}$ 

[Brake]

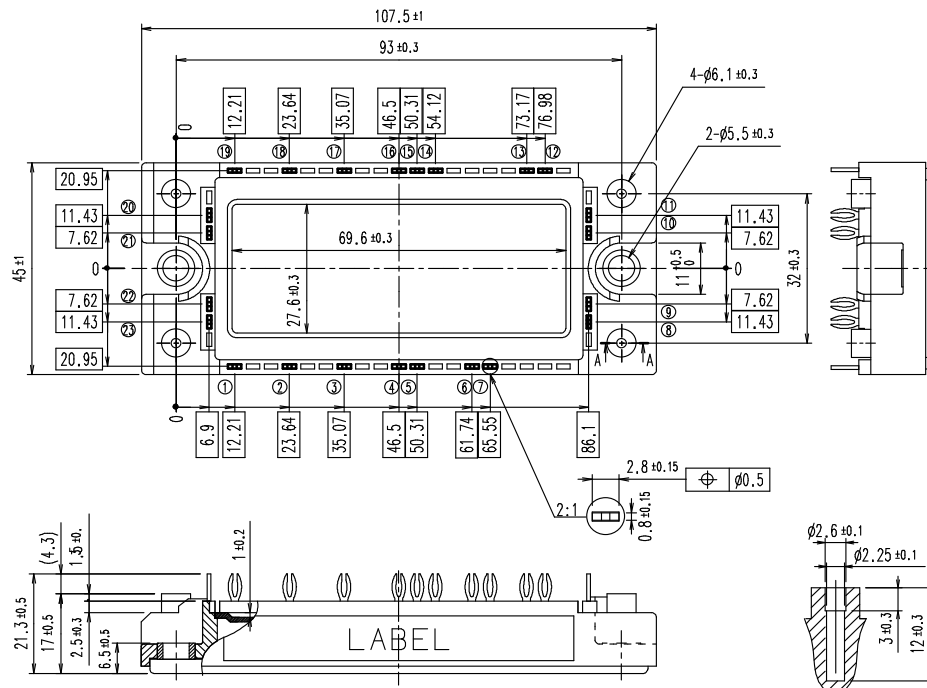
Dynamic gate charge (typ.)

 $V_{CC} = 600\text{V}$, $I_C = 25\text{A}$, $T_j = 25^\circ\text{C}$ 

Outline Drawings (Unit:mm)

□ shows theoretical dimension.

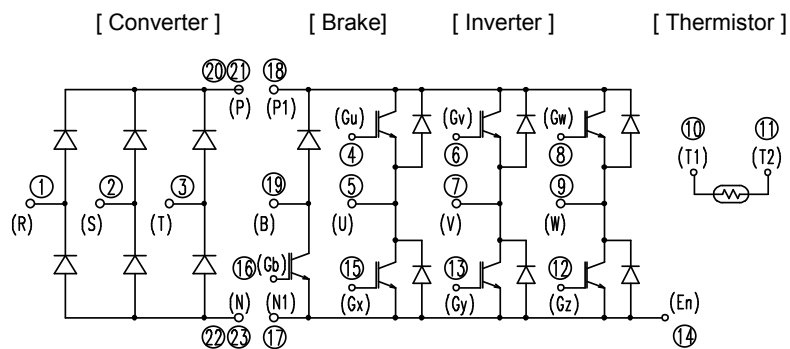
() shows reference dimension.



Section A-A

Weight: 200g(typ.)

Equivalent Circuit



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IGBT Modules

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